

Qualifying 65 nm CMOS monolithic active pixel sensors for cylindrical, lightweight vertex detectors

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EURIZON short presentations

27 July 2023

Feasibility of a lightweight vertex detector for the ALICE experiment

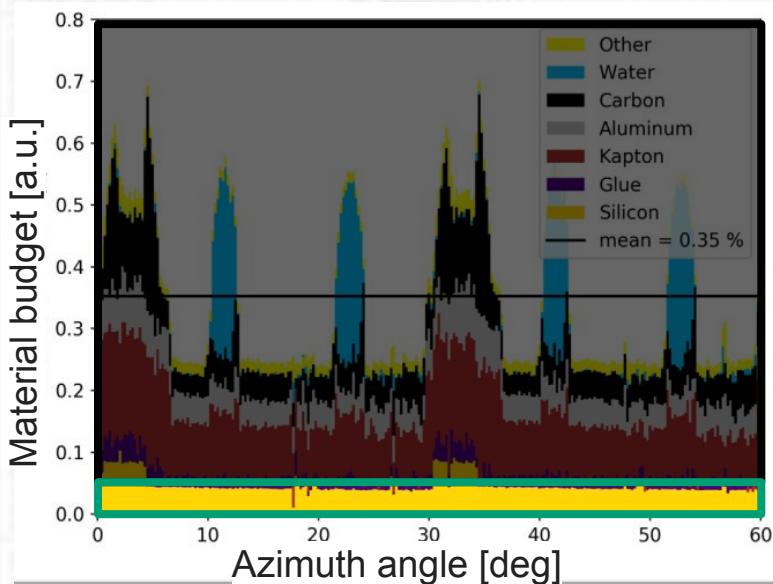


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ALICE

Pascal Becht (pascal.becht@cern.ch) | EURIZON detector school | 27 July 2023



Motivation:

- Material distorts tracking performance
- **Only silicon** is the **sensitive** part
- Can we get rid of the rest?
 - **Self-supporting, air-cooled sensors**



Ingredients:

- Monolithic active pixel sensors ([M. Deveaux - MAPS](#))
 - Integration on one wafer
 - Ultra thin sensors
- **Bent sensors**
 - Mechanical stability
- **Wafer-scale sensors**
 - No interconnections between small single sensors
- **65 nm CMOS technology**
 - Large wafers (30 cm)
 - “Intelligent”, small pixels

One of the first prototype sensors
in 65 nm CMOS technology

Bonding pads

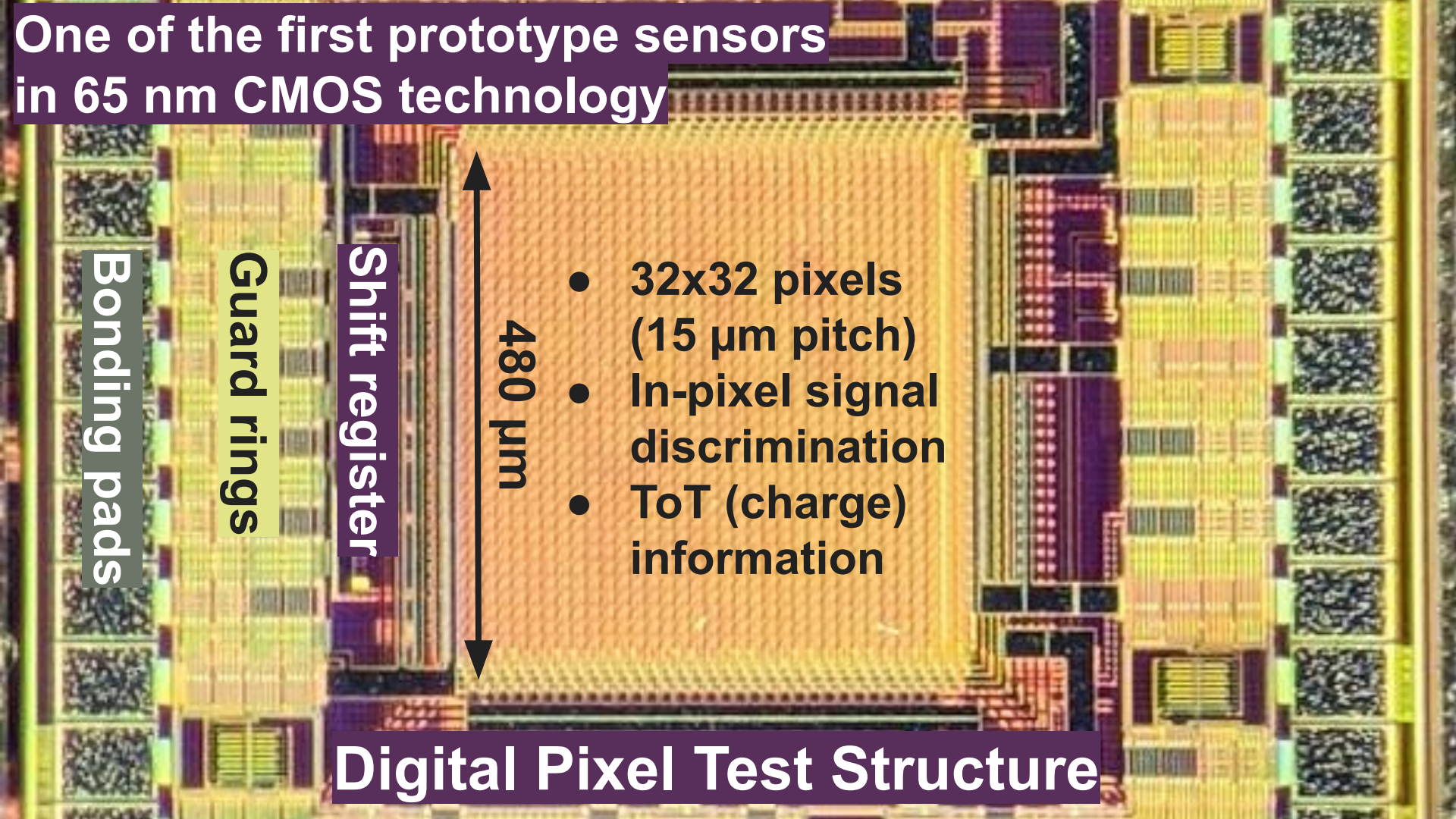
Guard rings

Shift register

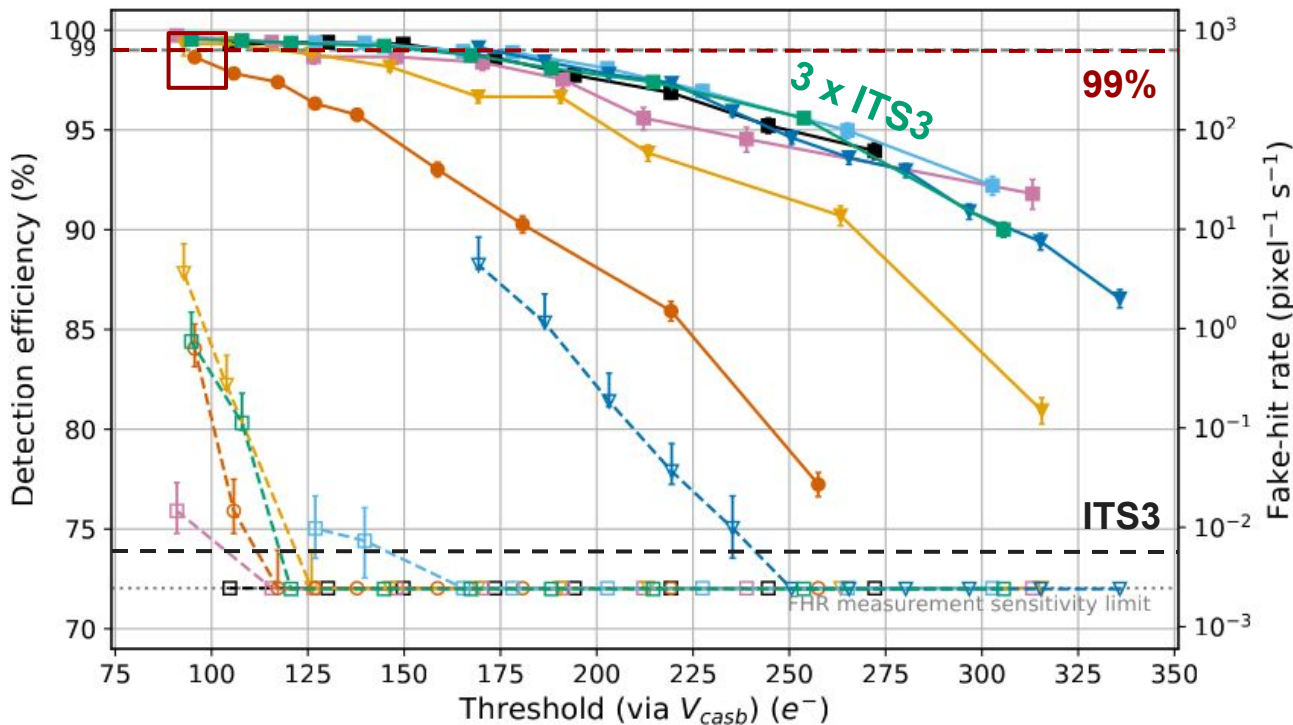
480 μm

- 32x32 pixels (15 μm pitch)
- In-pixel signal discrimination
- ToT (charge) information

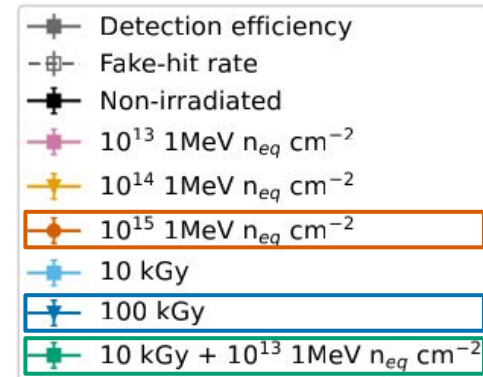
Digital Pixel Test Structure



65 nm CMOS technology well suited for MAPS in the ITS3 and beyond



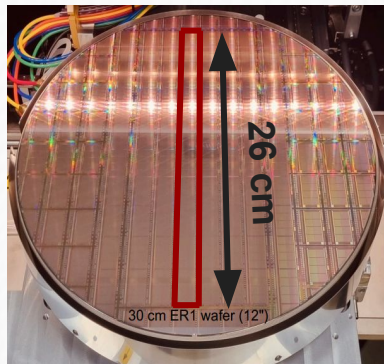
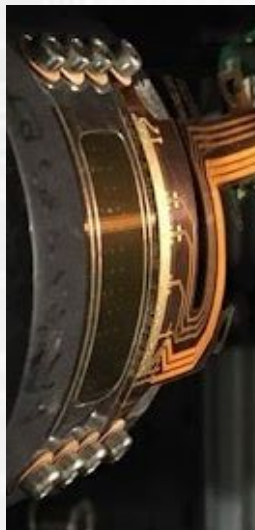
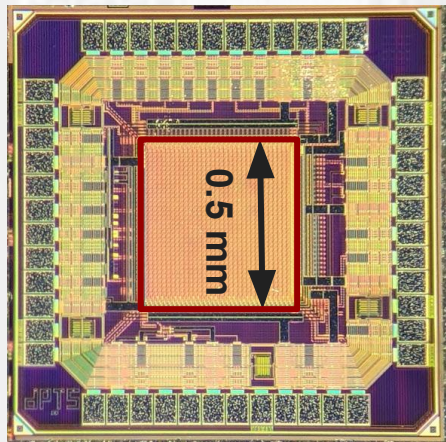
DPTS @ 20 °C (no cooling)



Association window:
480 μm x 1.5 μs

- Performance exceeds ITS3 requirements
- 99% detection efficiency in reach for highest irradiation levels

On the way to a cylindrical wafer-scale chip produced in 65 nm CMOS technology



What we have:

- **65 nm CMOS technology** is suitable and sufficiently radiation hard
 - DPTS and other prototypes
- **Bending of MAPS** is feasible
- **Stitching to achieve operable wafer-scale sensors** is possible

How it should look like in ~2 years:

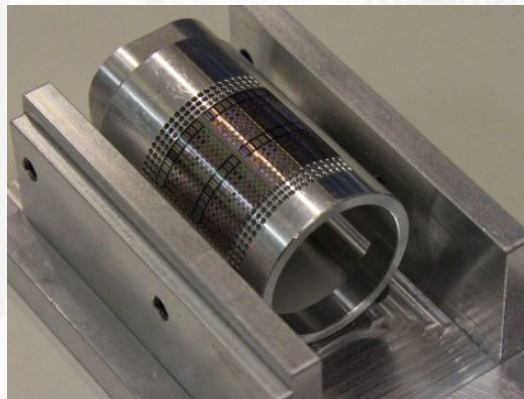
- **Full-scale vertex detector**
- To be inserted as the 3 innermost layers of the ALICE inner tracking system
- Until then:
 - Characterize
 - Develop
 - Understand

References and a quick getting started with the ITS3 project

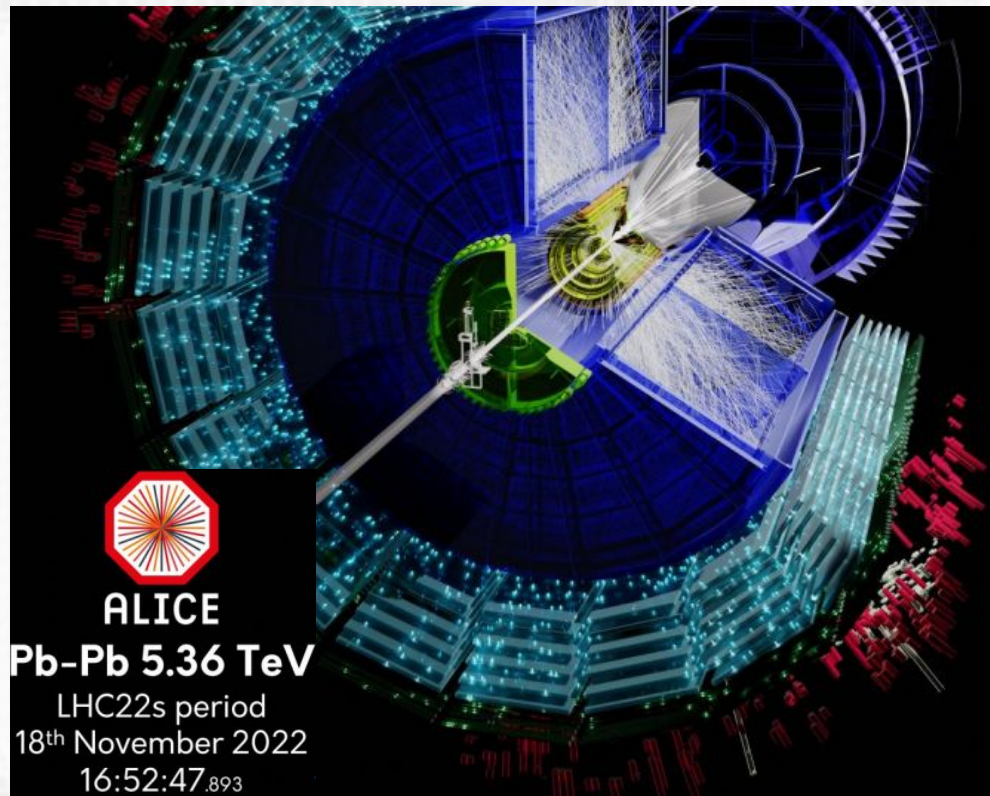


- [ITS3 overview paper](#)
- [ITS3 summary slides](#)
- [Mechanics and cooling](#)
- [DPTS performance paper](#)

Stay tuned for more!



65 nm CMOS sensors
First bent



Event displays like this with
the ITS3 included



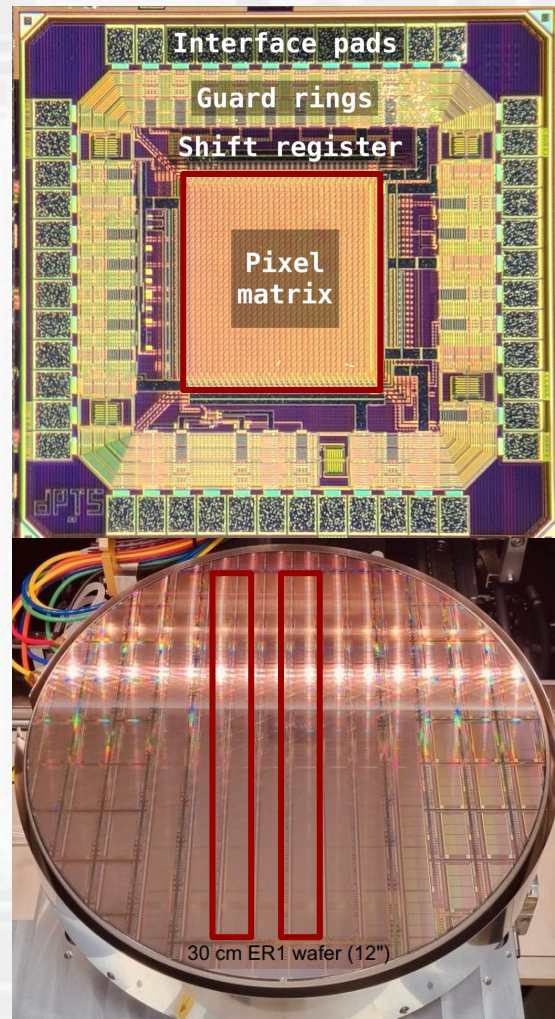
Auxiliary slides

The next ALICE inner tracker upgrade: sensors

- Improve tracking performance by reduction of material budget
 - E.g. pointing resolution by factor 2
 - Especially in low-momentum regime
- Truly cylindrical pixel detector wrapped around the beam pipe
 - Closer to interaction point
 - Less mechanical support
 - New beam pipe
- Cooled by airflow
- Waferscale sensors

ITS3 implies change to 65 nm CMOS technology node

- 30 cm diameter wafers, stitching possible
- Small pixel/feature size (occupancy)
- Two submissions so far (MLR1, ER1)



Digital Pixel Test Structure (DPTS)

- 32x32 px
- 15 μm pitch
- 480 μm x 480 μm

Monolithic Stitched Sensor (MOSS)

- 6.72 Mpx
- 18/22.5 μm pitch
- 1.4 cm x 25.9 cm

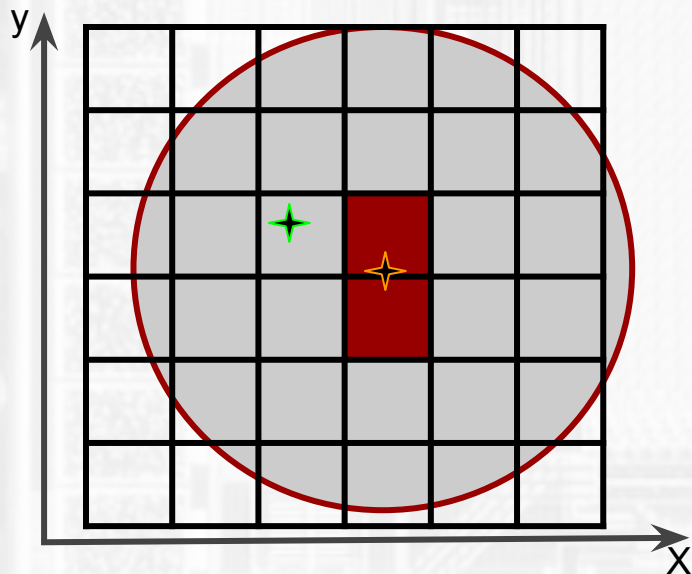
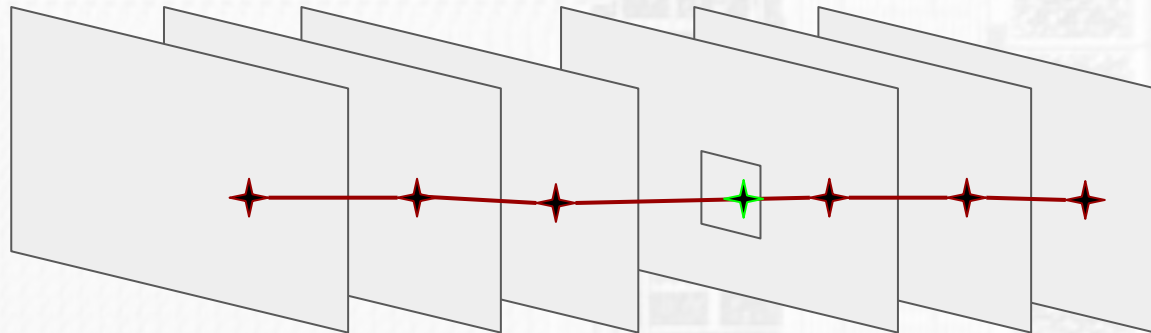


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Testbeam data analysis

- Track fitting from reference planes
- GBL model used
- Multiple scattering taken into account
- **Interpolation** to DUT
- Associate **measured DUT cluster**

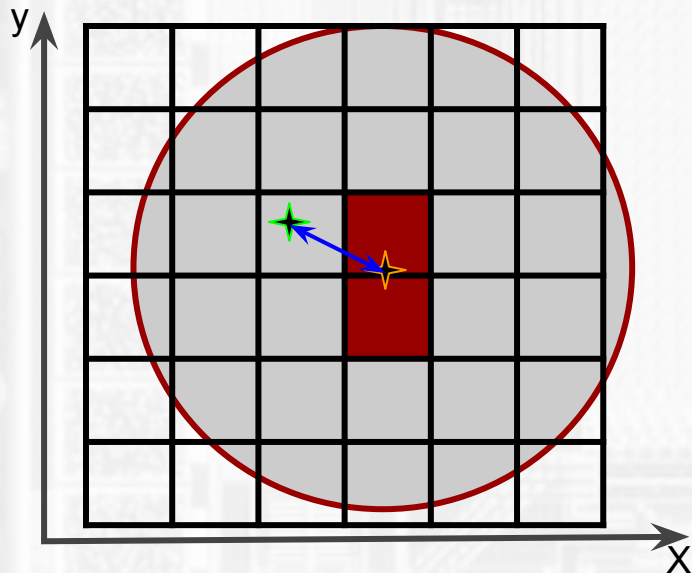


Efficiency calculation

- No spatial window
 - Undecodable events considered: “Signal clash”
 - Trigger mitigates false hit associations
- Time window: 1.5 μ s
- Number-ratio of **matched tracks** and total reconstructed tracks

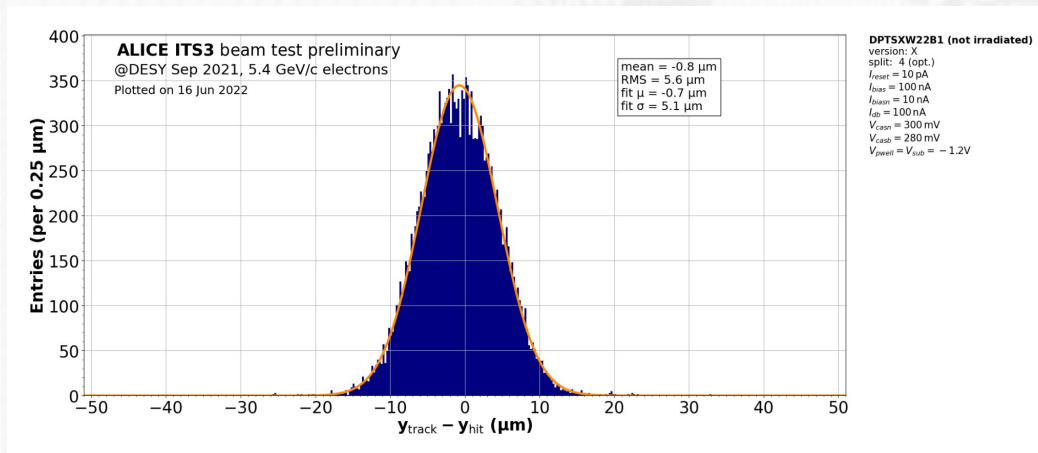
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Position resolution calculation

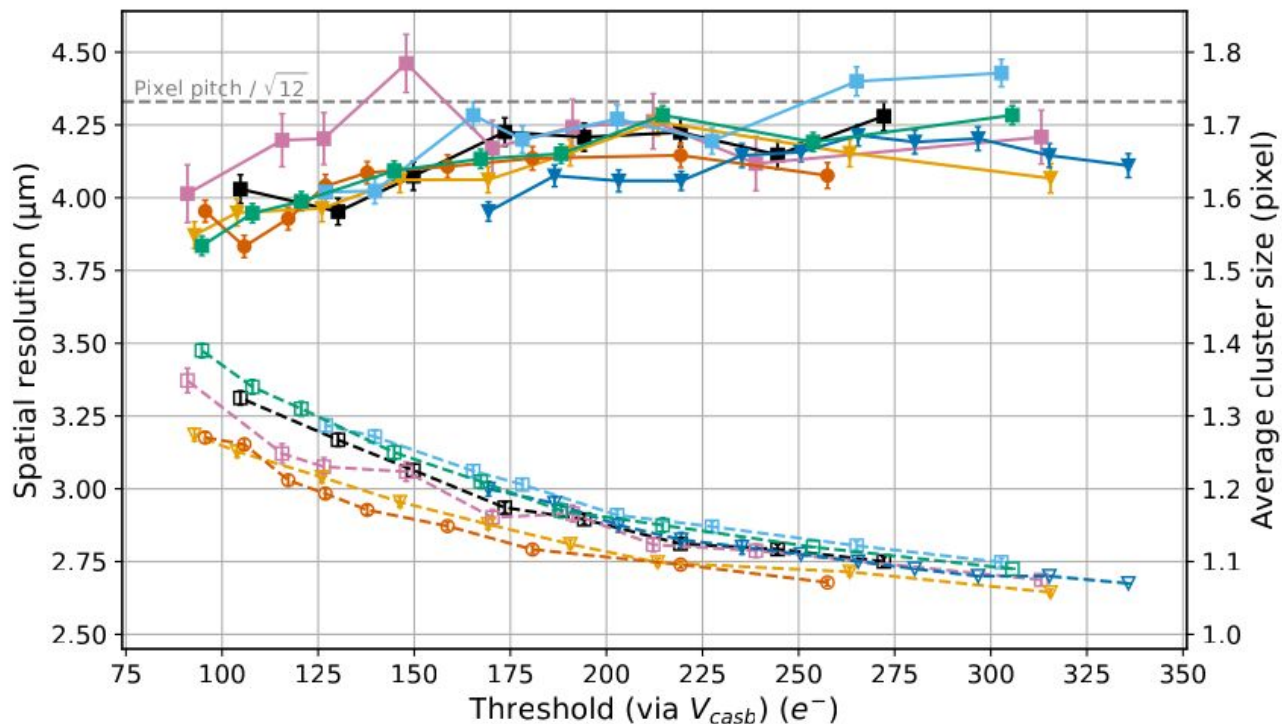
- Spatial window: $45 \mu\text{m}$ (3 px)
- Time window: $1.5 \mu\text{s}$



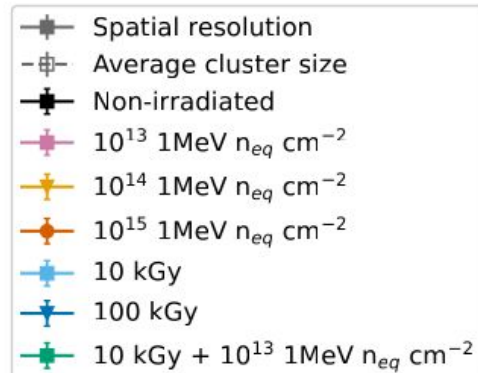
- Width of **spatial residual distribution** in x and y
 - Arithmetic mean
- Subtract telescope resolution from simulation: $2.43 \mu\text{m}$

DPTS performance - Spatial resolution

Irradiated sensors



DPTS @ 20 °C (no cooling)



Association window:
45 μm x 1.5 μm

- No strong dependence on irradiation level
- Visible cluster size ordering according to NIEL dose